

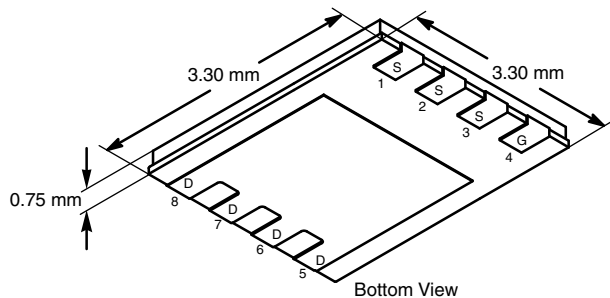


## N-Channel 30 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ ) (Max.)	$I_D$ (A) <sup>f</sup>	$Q_g$ (Typ.)
30	0.0075 at $V_{GS} = 10$ V	38.3	6.9 nC
	0.0120 at $V_{GS} = 4.5$ V	30.2	

Thin PowerPAK® 1212-8



Ordering Information:  
 SiS322DNT-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

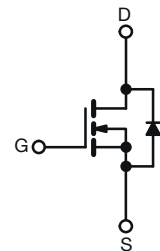
- TrenchFET® Gen IV Power MOSFET
- 100 %  $R_g$  and UIS Tested
- Thin 0.75 mm height
- Material categorization:  
 For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Switch Mode Power Supplies
- Personal Computers and Servers
- Telecom Bricks
- VRM's and POL



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	+ 20, - 16	
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	38.3
		$T_C = 70$ °C	30.6
		$T_A = 25$ °C	15.3 <sup>a, b</sup>
		$T_A = 70$ °C	12.1 <sup>a, b</sup>
Pulsed Drain Current ( $t = 300$ $\mu$ s)	$I_{DM}$	70	A
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	
		$T_A = 25$ °C	2.9 <sup>a, b</sup>
Single Pulse Avalanche Current	$I_{AS}$	10	mJ
Single Pulse Avalanche Energy	$E_{AS}$	5	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	19.8
		$T_C = 70$ °C	12.7
		$T_A = 25$ °C	3.2 <sup>a, b</sup>
		$T_A = 70$ °C	3 <sup>a, b</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>c, d</sup>		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, e</sup>	$R_{thJA}$	31	39	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	5	6.3	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10$  s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The Thin PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 81 °C/W.
- Based on  $T_C = 25$  °C.

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		18.5		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-5.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.4	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = +20\text{ V}, -16\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.0060	0.0075	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		0.0096	0.0120	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		54		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1000		pF
Output Capacitance	$C_{oss}$			287		
Reverse Transfer Capacitance	$C_{rss}$			34		
$C_{rss}/C_{iss}$ Ratio				0.034	0.068	
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		14.3	21.5	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		6.9	10.5	
Gate-Source Charge	$Q_{gs}$			2.8		
Gate-Drain Charge	$Q_{gd}$			1.6		
Output Charge	$Q_{oss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		7.8		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.4	1.6	3.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		15	30	ns
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			15	30	
Fall Time	$t_f$			7	14	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		11	22	
Rise Time	$t_r$			9	18	
Turn-Off Delay Time	$t_{d(off)}$			15	30	
Fall Time	$t_f$			5	10	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			18	A
Pulse Diode Forward Current	$I_{SM}$				70	
Body Diode Voltage	$V_{SD}$	$I_S = 5\text{ A}, V_{GS} = 0\text{ V}$		0.77	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		19	35	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			7	14	nC
Reverse Recovery Fall Time	$t_a$			10		ns
Reverse Recovery Rise Time	$t_b$			9		

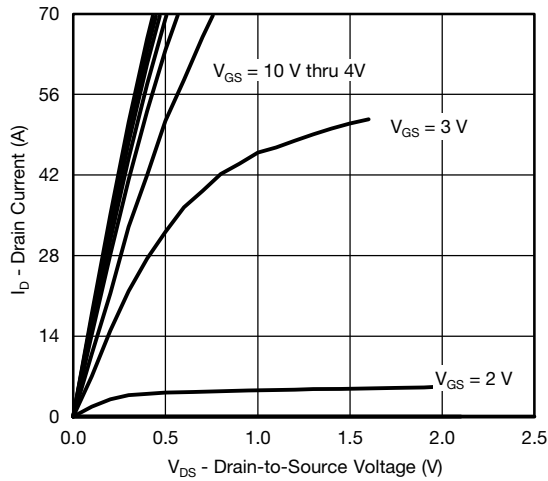
## Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing.

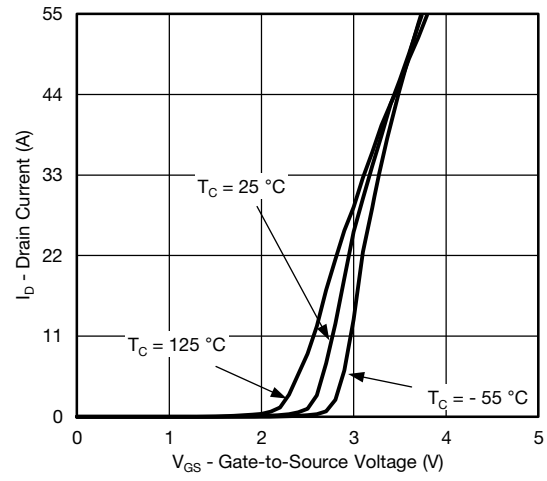
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



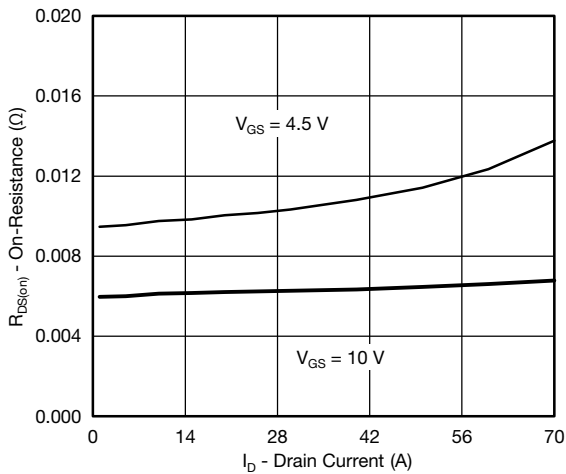
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



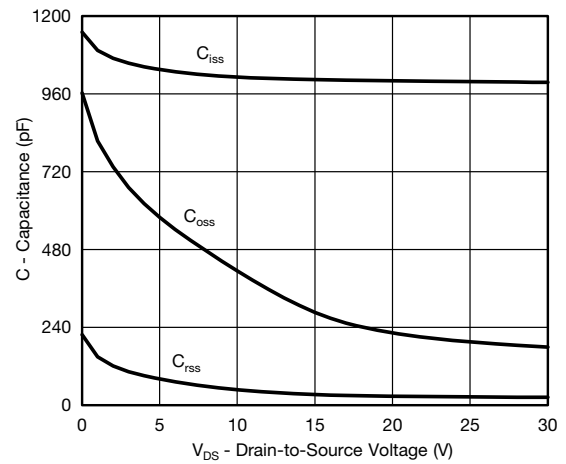
**Output Characteristics**



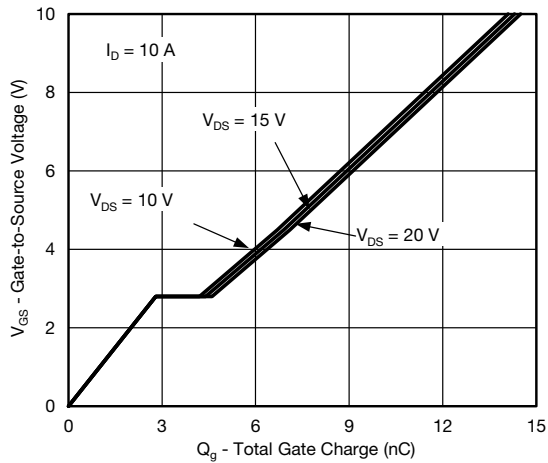
**Transfer Characteristics**



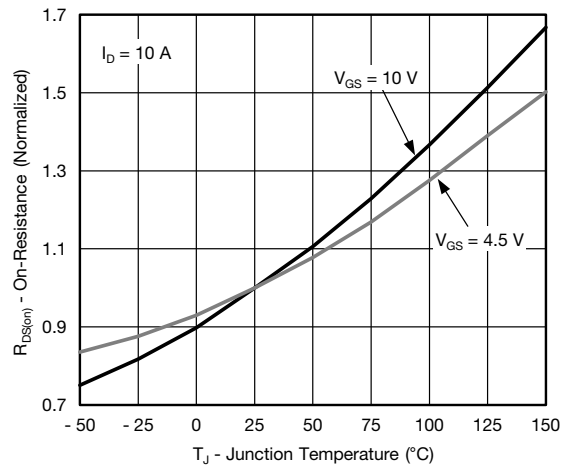
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



**Gate Charge**



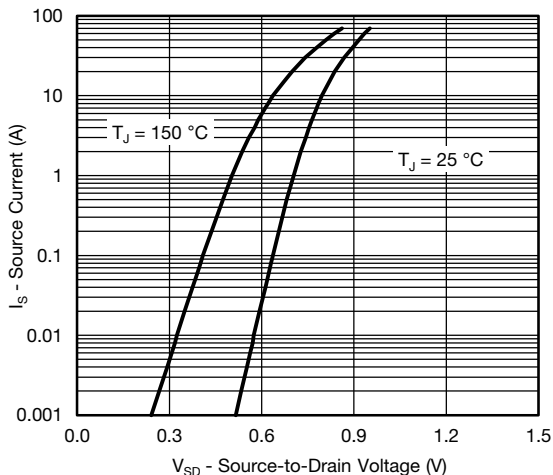
**On-Resistance vs. Junction Temperature**

# SiS322DNT

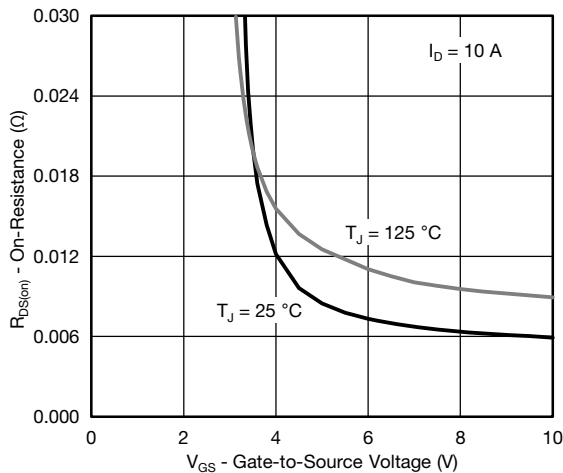
Vishay Siliconix



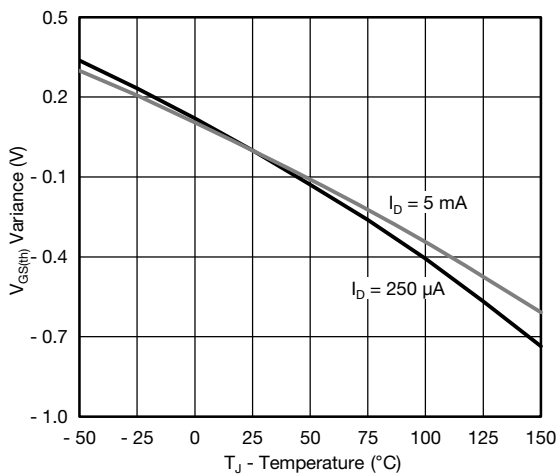
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



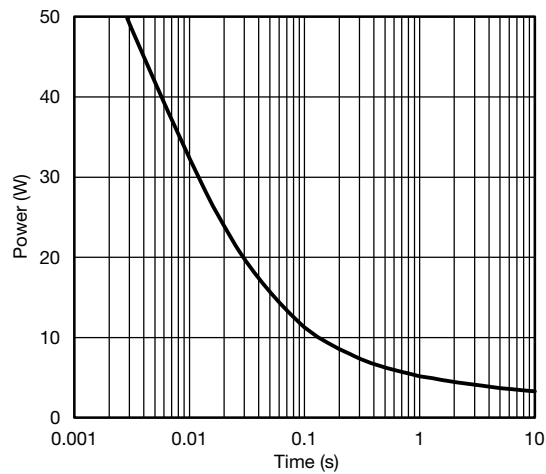
Source-Drain Diode Forward Voltage



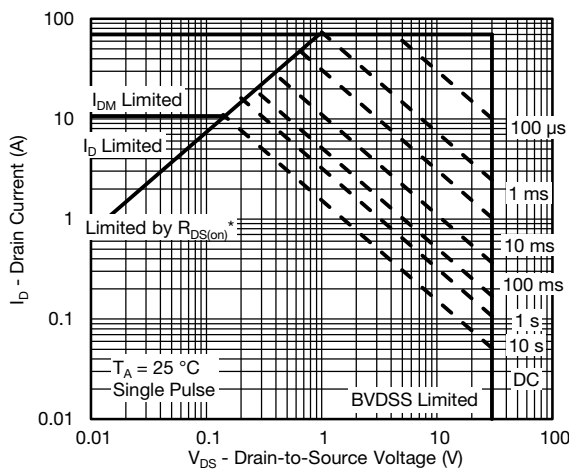
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



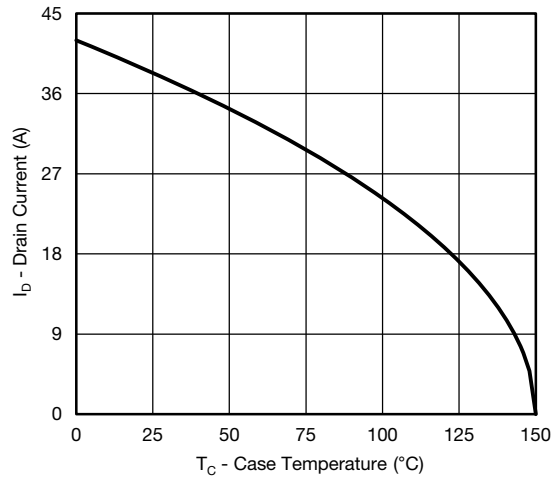
Single Pulse Power, Junction-to-Ambient



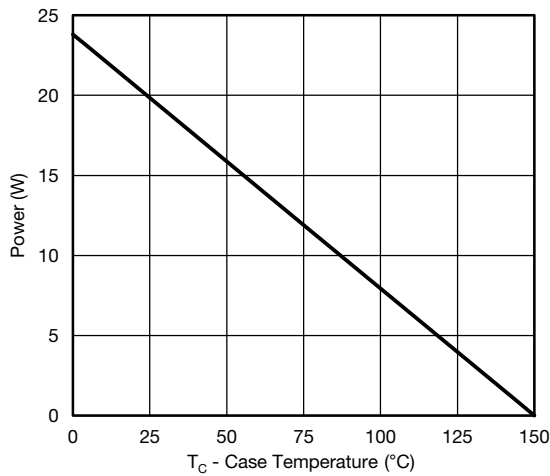
Safe Operating Area, Junction-to-Ambient



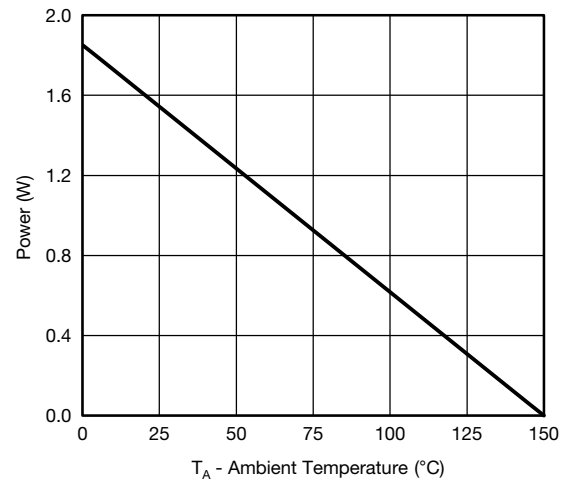
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



**Power, Junction-to-Case**



**Power, Junction-to-Ambient**

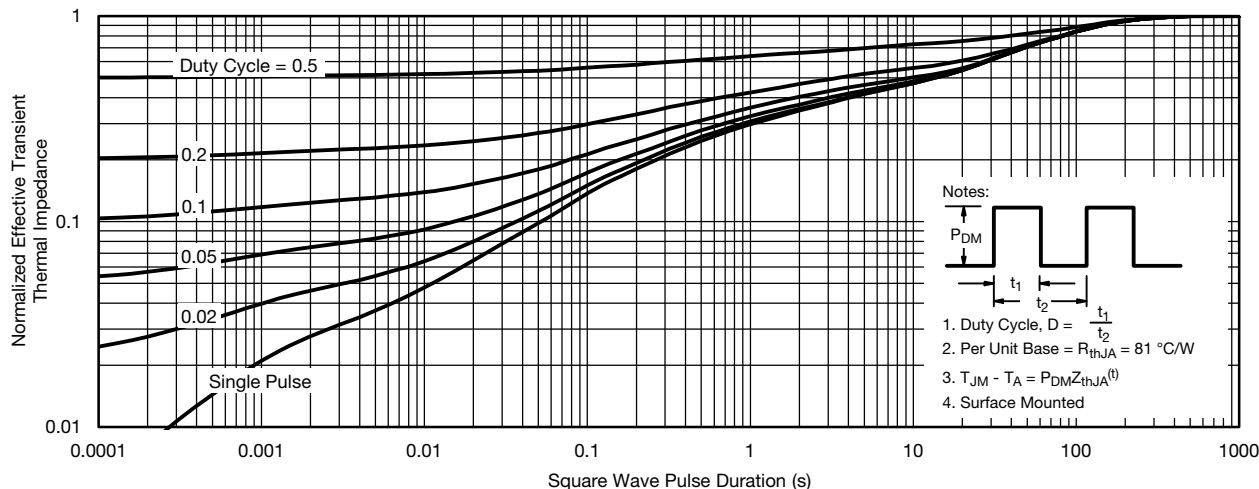
\* The power dissipation P<sub>D</sub> is based on T<sub>J(max.)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

# SiS322DNT

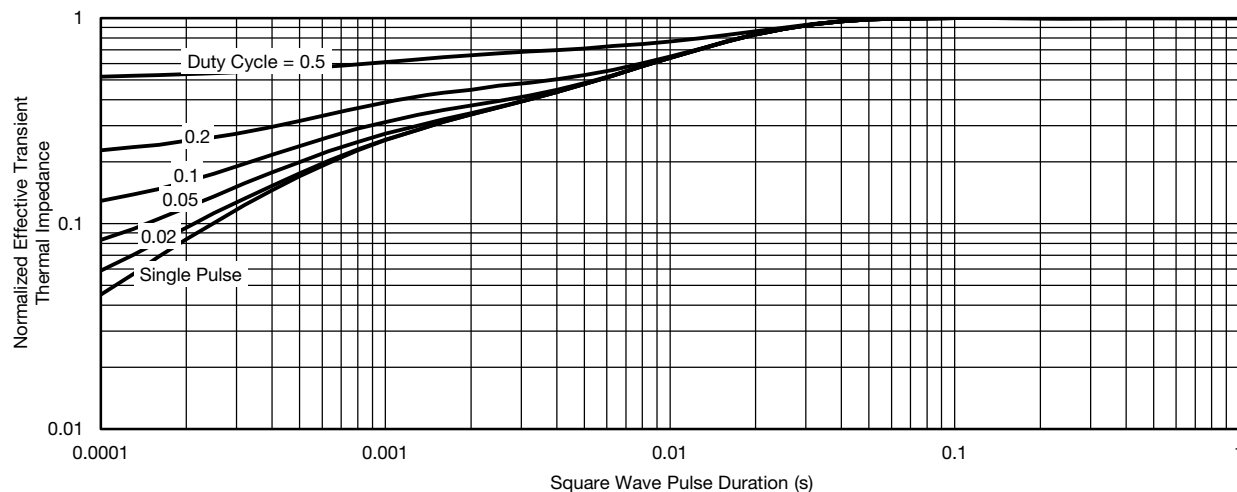
Vishay Siliconix



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

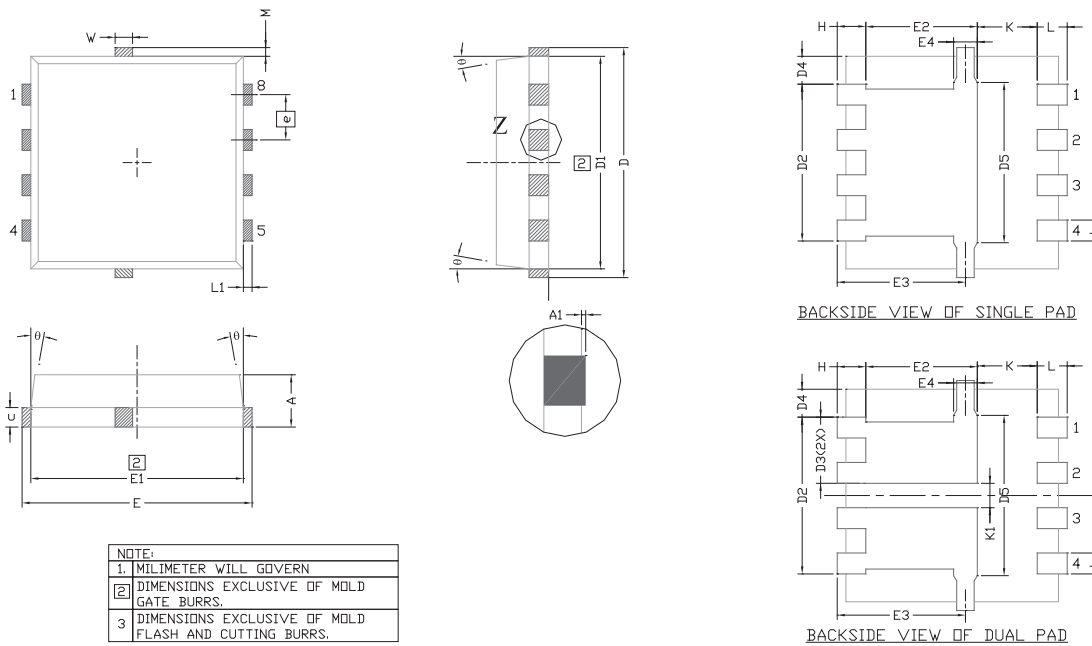


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?63569](http://www.vishay.com/ppg?63569).



PowerPAK® 1212-8T



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	-	0.05	0.000	-	0.002
b	0.23	0.30	0.41	0.009	0.012	0.016
c	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D3	0.48	-	0.89	0.019	-	0.035
D4	0.47 TYP.			0.0185 TYP.		
D5	2.3 TYP.			0.090 TYP.		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4	0.34 TYP.			0.013 TYP.		
e	0.65 BSC			0.026 BSC		
K	0.86 TYP.			0.034 TYP.		
K1	0.35	-	-	0.014	-	-
H	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 TYP.			0.005 TYP.		

ECN: T13-0056-Rev. A, 18-Feb-13  
DWG: 6012



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Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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## JONHON

«JONHON» (основан в 1970 г.)

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(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А